Comchip
SMD Diode Specialist

New Product Announcement

CSFMT101-HF Thru. CSFMT108-HF

Low Profile SMD Super Fast Recovery Rectifiers

Package: SOD-123H / MINI SMA (Molded Plastic)

Reverse Voltage: 50 to 600 Volts

Forward Current: 1.0 Amp

RoHS Device

Halogen Free

Excellent power dissipation offers better reverse leakage current and thermal resistance

Low profile package is 40% thinner than standard SOD-123 package

Low power loss, high efficiency

High current capability, low forward voltage drop.

High surge capability

Guarding for over voltage protection

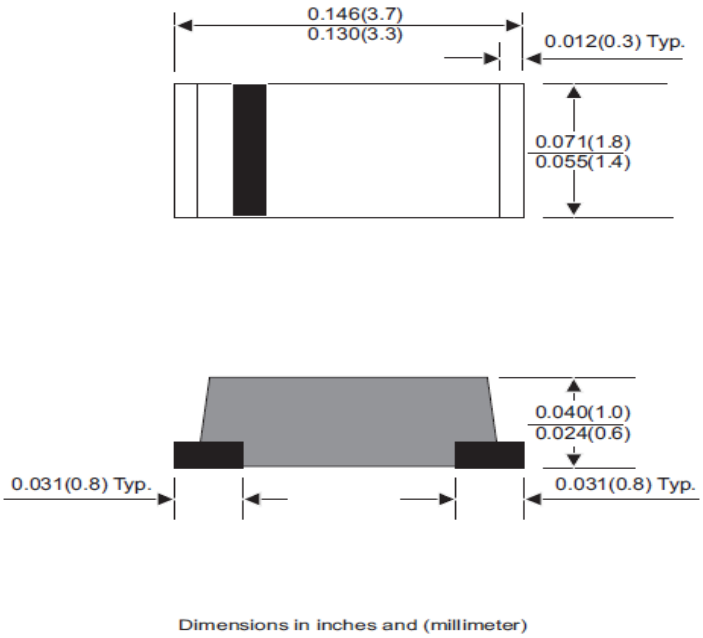
Ultra high-speed switching

Silicon epitaxial planar chip, metal silicon junction.

Lead-free part meets environmental standards of MIL-STD-19500/228

Comchip's CSFMT super fast recovery rectifier series utilizes the low profile flat chip SOD-123H (MINI SMA) package. The SOD-123H measures just: 1.6mm(w) x 3.5mm(l) x 0.8mm(h). The slim package design makes the CSFMT series ideal for components of DC power supplies and high-voltage direct current power transmission systems. With today's market demanding smaller and thinner products, Comchip is striving to exceed market demands with quality products at a conveniently low price. With a forward current of 1 amp, reverse voltage applications range from 50 to 600 volts.

SOD-123H



Dimensions in inches and (millimeter)

Epoxy: UL94-V0 rated flame retardant

Terminals: Solderable per MIL-STD-750, Method 2026

Polarity: Indicated by cathode band

Mounting Position: Any

Weight: 0.011 grams

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Maximum Ratings (at T_A=25°C unless otherwise noted)

Parameter		Symbol	CSFMT 101-HF	CSFMT 102-HF	CSFMT 103-HF	CSFMT 104-HF	CSFMT 105-HF	CSFMT 106-HF	CSFMT 107-HF	CSFMT 108-HF	Unit
Max. repetitive peak reverse voltage		V_{RRM}	50	100	150	200	300	400	500	600	V
Max. Continuous rever voltage		V_R	50	100	150	200	300	400	500	600	V
Max. RMS voltage		V_{RMS}	35	70	105	140	210	280	350	420	V
Max. averaged forward current		I_O	1.0								A
Max. Forward voltage @ I_F=1.0A		V_F	0.95				1.25		1.70		V
Reverse recovery time (Note 1)		T_{RR}	35								ns
Max. Forward surge current 8.3ms singe half sine-wave superimposed on rated load (JEDEC method)		I_{FSM}	25								A
Max. Reverse current	V_R=V_{RRM} T_J=25°C	I_R	5.0								μA
	V_R=V_{RRM} T_J=100°C		100								
Typ. Thermal resistance Junction to ambient air		$R_{\theta JA}$	42								°C/W
Typ. Junction capacitance f=1MHz and applied 4V DC reverse voltage		C_J	10								pF
Operating junction temperature		T_J	-55 to +150								°C
Storage temperature		T_{STG}	-65 to +175								°C

Note 1. Reverse recovery time test condition,I_F=0.5A,I_R=1.0A,I_{RR}=0.25A

RoHS HALOGEN